杰力科技股份有限公司
Excelliance MOS Corporation

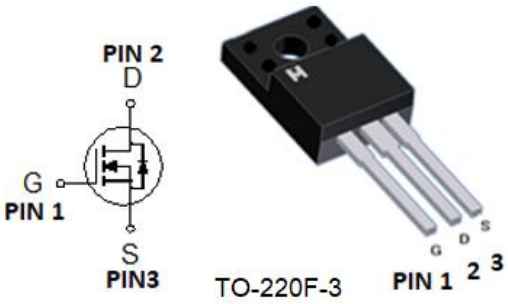
EMD60N15F

Single N-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

BV_{DSS}	150V
$R_{DSON\ (MAX.)}$	60mΩ
I_D	20A

Pin Description:



Single N Channel MOSFET

UIS, Rg 100% Tested

Pb-Free Lead Plating & Halogen Free

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Drain-Source Voltage		V_{DSS}	150	V
Gate-Source Voltage		V_{GS}	±30	V
Continuous Drain Current	T_C = 25 °C	I_D	20	A
	T_C = 100 °C		12	
Pulsed Drain Current[1]		I_{DM}	80	
Avalanche Current		I_{AS}	18	
Avalanche Energy	L = 0.2mH, ID=18A, RG=25Ω	E_{AS}	32.4	mJ
Repetitive Avalanche Energy[2]	L = 0.1mH	E_{AR}	16.2	
Power Dissipation	T_C = 25 °C	P_D	35	W
	T_C = 100 °C		14	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	$R_{\theta JC}$		3.5	°C / W
Junction-to-Ambient	$R_{\theta JA}$		62.5	

[1]Pulse width limited by maximum junction temperature.

[2]Duty cycle ≤ 1%

[3]Pulsed drain current rating is package limited.

ELECTRICAL CHARACTERISTICS (T_C = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	150			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2.0	3.0	4.5	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±30V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 120V, V_{GS} = 0V			1	μA
		V_{DS} = 100V, V_{GS} = 0V, T_J = 125 °C			25	
On-State Drain Current[1]	$I_{D(ON)}$	V_{DS} = 10V, V_{GS} = 10V	20			A
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 20A		50	60	mΩ
		V_{GS} = 7V, I_D = 20A		58	70	
Forward Transconductance[1]	g_{fs}	V_{DS} = 5V, I_D = 20A		25		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		2903		pF
Output Capacitance	C_{oss}			172		
Reverse Transfer Capacitance	C_{rss}			59		
Gate Resistance	R_g	V_{GS} = 15mV, V_{DS} = 0V, f = 1MHz		2.3		Ω
Total Gate Charge[1,2]	Q_g	V_{DS} = 80V, V_{GS} = 10V, I_D = 20A		38.2		nC
Gate-Source Charge[1,2]	Q_{gs}			9.8		
Gate-Drain Charge[1,2]	Q_{gd}			14.5		
Turn-On Delay Time[1,2]	$t_{d(on)}$	V_{DS} = 75V, I_D = 1A, V_{GS} = 10V, R_{GS} = 6Ω		15		nS
Rise Time[1,2]	t_r			40		
Turn-Off Delay Time[1,2]	$t_{d(off)}$			45		
Fall Time[1,2]	t_f			38		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_C = 25 °C)						
Continuous Current	I_S				20	A
Pulsed Current[3]	I_{SM}				80	
Forward Voltage[1]	V_{SD}	I_F = I_S, V_{GS} = 0V			1.3	V
Reverse Recovery Time	t_{rr}	I_F = 20A, dI_F/dt = 100A / μS		100		nS
Reverse Recovery Charge	Q_{rr}			360		nC

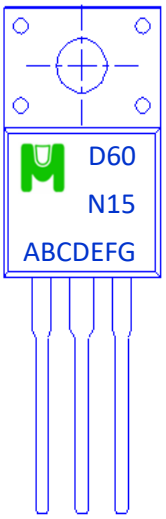
[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

[2]Independent of operating temperature.

[3]Pulse width limited by maximum junction temperature.

Ordering & Marking Information:

Device Name: EMD60N15F for TO-220F



D60N15: Device Name

ABCDEFG: Date Code

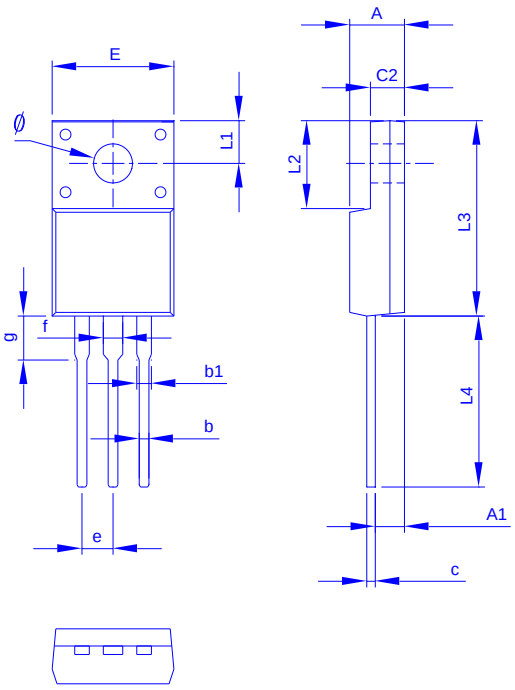
A: Assembly House

B: Year(A:2008 B:2009 C:2010….)

C: Month(A:01 B:02 C:03 D:04 E:05 F:06 G:07 H:08 I:09 J:10 K:11 L:12)

DEFG: Serial No

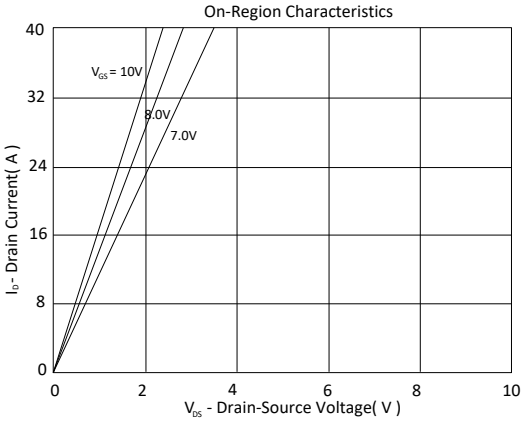
Outline Drawing

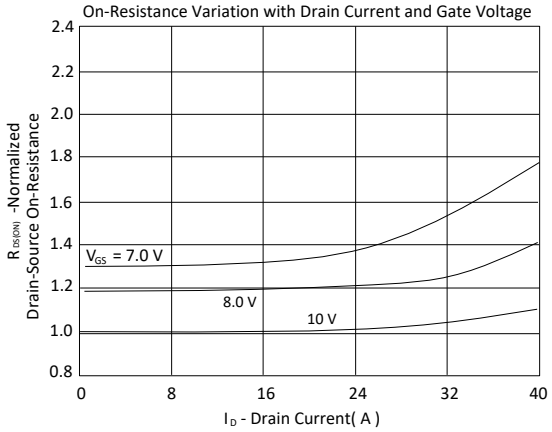


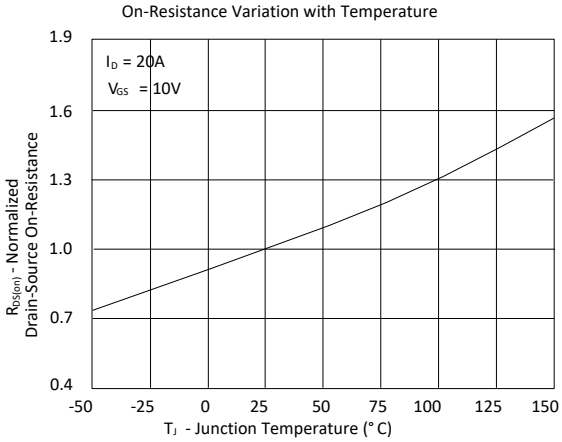
Dimension in mm

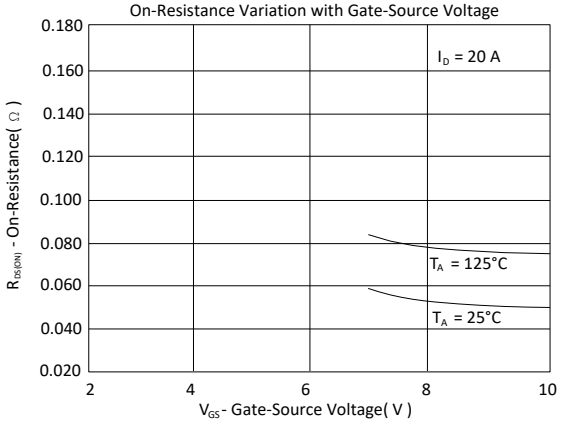
Dimension	A	A1	b	b1	c	c2	E	L1	L2	L3	L4	ø	e	f	g
Min.	4.3	2.49	0.5	1.1	0.4	2.34	9.96	2.7	6.48	14.8	12.65	3	2.44	1.17	2.93
Typ.	4.5	2.59	0.8	1.3	0.5	2.54	10.1	3.25	6.68	15.87	12.98	3.1	2.54	1.28	3.03
Max.	4.9	2.96	0.95	1.6	0.75	3.2	10.36	3.45	6.9	16.2	13.5	3.38	2.64	1.75	4

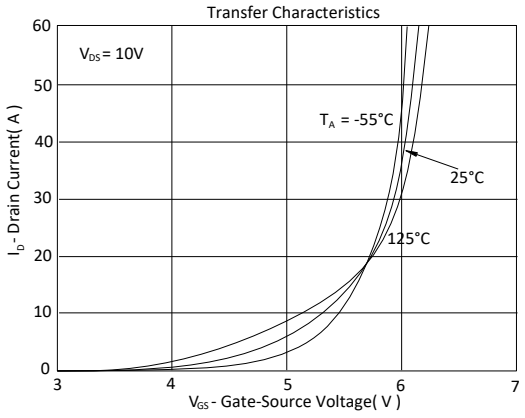
TYPICAL CHARACTERISTICS

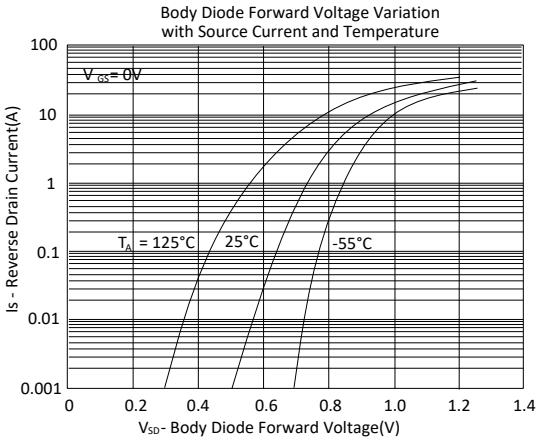




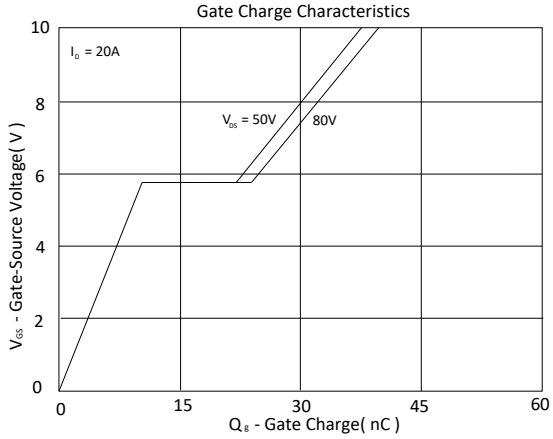




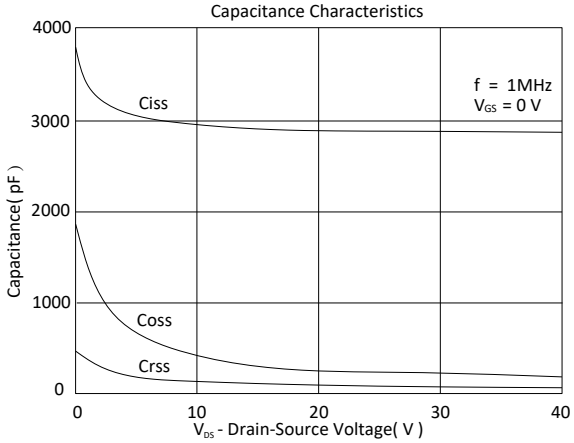




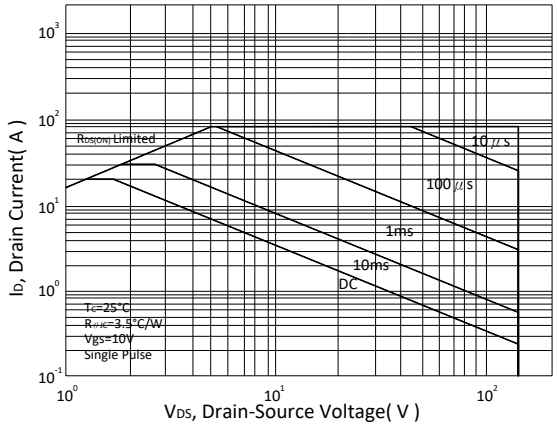
Gate Charge Characteristics



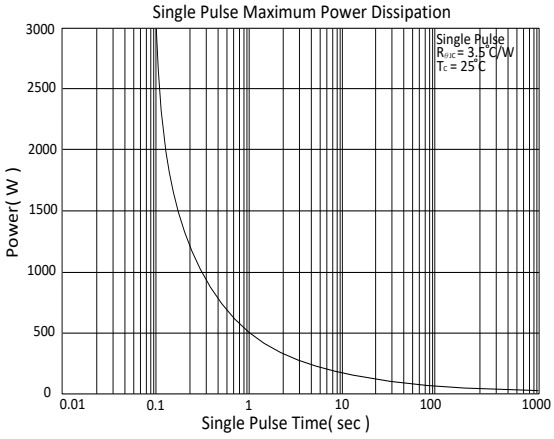
Capacitance Characteristics



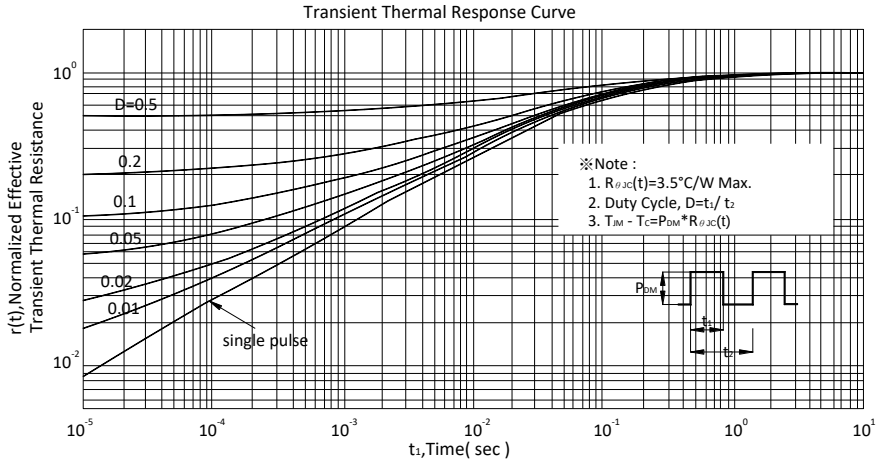
Maximum Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



◆ Tube Information:50pcs/Tube (1000pcs/Box)